Topological Edge and Corner States in Biphenylene Network

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(Dated: January 29, 2024)

The electronic states and topological properties of the biphenylene network (BPN) are analyzed using a tight-binding model based on the π -electron network. It is shown that tuning the hopping parameters induces topological phase transitions, leading to the emergence of edge states owing to the nontrivial topological Zak phase of the bulk BPN. Elementary band analysis clearly gives the number of edge states, which are associated with the location of Wannier centers. In addition, we have presented the conditions for the emergence of corner states owing to the higher-order topological nature of BPN.

I. INTRODUCTION

The concept of topology has brought about the paradigm shift in modern condensed matter physics, opening up the research field of topological materials. These materials include topological insulators [1–10], topological crystalline insulators [11–13], topological semimetals [14–19] and so on. One of the essential properties of topologically nontrivial systems is the bulk-edge correspondence, where robust edge and surface states appear at the interfaces that separate two topologically distinct systems. These topologically protected states are insensitive to local perturbation such edge roughness and disorder, which may serve for the application to the ultralow-power-consumption electronics and quantum computation. The idea of device design based on topology has also been recently applied to photonics [20–23] and other systems [24, 25].

In a system with both time reversal and crystal inversion symmetries, the Zak phase can serve as a good topological invariant for characterizing the bulk-edge correspondence [26]. Since the Zak phase is associated with charge polarization [27-31], a nontrivial finite Zak phase predicts the presence of edge-localized states when an edge is introduced to the system. In graphene, a one-atomic thickness two-dimensional (2D) carbon sheet, the edges induce the electron localized states (edge states) at the Fermi energy [32-34]. However, the edge states crucially depend on the shape of edges and are absent for armchair edges. This puzzle can be resolved by considering the Zak phase of the bulk wave function of graphene, which gives the momentum dependent Zak phase [35, 36]. The Zak phase is identically zero solely for the armchair edge, i.e., no edge states, which is consistent with various numerical calculations [37, 38]. The presence of edge states provides the spin polarization [32, 39] and a perfectly conducting channel [40].

Recently, biphenylene network (BPN), a newly synthesized 2D sp²-carbon-based material, was successfully synthesized by Fan *et.al.* [41]. BPN has a fascinating lattice structure, where the hexagonal carbon rings are organized on a square lattice, resulting in a 2D tiling pattern that includes four-, six-, and eight-membered rings. Previous studies have reported thermal conductivity, magnetic properties, and hydrogen stor-

age properties based on first-principles calculations [42–45]. Also, Ref. [44] reported Zak phases and topological grain boundary states along BPN nanoribbons. However, the higher order topological corner states are not considered yet. Here we also employ the elementary band analysis which clearly gives the number of edge states, which are associated with the location of Wannier centers.

In this paper, we theoretically study the electronic and topological properties of 2D BPN. Since BPN comprises only sp^2 carbon atoms similar to graphene, the π -electrons govern the electronic states of BPN near the Fermi energy. Thus, we employ the tight-biding model, which describes π -electronic states of 2D BPN to analyze the topological properties. We will demonstrate that successive topological phase transitions occur by tuning the ratio between intra- and inter-cellular electron hoppings. In Su-Schrieffer-Heeger (SSH) model [46, 47], similar topological phase transition can occur, inducing nontrivial Zak phase, resulting in the edge states [36, 48–50]. We also find that the topological properties of BPN are characterized by the Zak phase of the bulk wave function. Charge polarization at the surfaces, i.e., edge states, is induced if the Zak phase possesses π . By studying BPN nanoribbons, we attribute the appearance of edge states to the Zak phase of π . Furthermore, we have demonstrated that the exact number of edge states can be determined by considering the position of the Wannier orbital. Similar arguments can be used to show the existence of topological corner states.

This paper is organized as follows. In Sec. II, we investigate the electronic states of π -electrons of BPN using a tightbinding model. Considering two types of hopping energies, we show that the topological phase transition occurs at a specific ratio. In Sec. III, we illustrated the existence of the edge states in BPN guaranteed by nontrivial Zak phase and the central position of Wannier function. In addition, we find multiple corner states in BPN nanoflake. Section IV provides the summary of the paper.



FIG. 1. (a) The lattice structure of BPN. The shaded region is the unit cell, with six nonequivalent sublattices of carbon atoms (A to F). $a_1 = (a, 0)$ and $a_2 = (0, a_T)$ are two primitive vectors, where a and $a_T = \frac{3a}{\sqrt{3}+1}$. The intra- (inter-) cellular hoppings denoted by red (black) lines are $\gamma(\gamma')$. (b) The 1st BZ of BPN and their high-symmetric points, $\Gamma = (0,0)$, $X = (\pi/a,0)$, $Y = (0,\pi/a_T)$, and $S = (\pi/a, \pi/a_T)$.

II. ELECTRONIC STATES OF 2D BPN

A. Tight-binding model

Figure 1 (a) displays the schematic of the lattice structure for 2D BPN, where the hexagonal carbon rings are organized on a square lattice, resulting in a 2D tiling pattern that includes four-, six-, and eight-membered rings. The shaded rectangle in Fig. 1 (a) represents the unit cell. Since the BPN is composed of sp² carbon atoms, the electronic states of 2D BPN near the Fermi energy are governed by π -electrons. Now let us consider the nearest-neighbor tight-binding model for π -electrons of 2D BPN. BPN contains six geometrically nonequivalent carbon atoms (A, B, C, D, E, F) in the unit cell as shown in Fig. 1 (a). Here, $a_1 = (a, 0)$ and $a_2 = (0, a_T)$ are the primitive vectors. a and $a_T = \frac{3a}{\sqrt{3}+1}$ are lattice periodicities along x- and y-directions, respectively. The length of a is 3.7554Å. We shall introduce two kinds of electron hoppings: γ is the intra-cellular hopping, and γ' is the inter-cellular hopping, respectively. Figure 1 (b) shows the first Brillouin zone (BZ) with high-symmetric points, i.e., $\Gamma = (0,0)$, $X = (\frac{\pi}{a},0)$, $Y = (0, \frac{\pi}{a_T})$, and $S = (\frac{\pi}{a}, \frac{\pi}{a_T})$. The actual parameter set to reproduce the energy band structure for π -electrons of 2D BPN is given in Appendix A.

The eigenvalue equation of 2D BPN is described as

$$\hat{H}(\boldsymbol{k}) | \boldsymbol{u}_{n,\boldsymbol{k}} \rangle = E_{n,\boldsymbol{k}} | \boldsymbol{u}_{n,\boldsymbol{k}} \rangle, \qquad (1)$$

where $\hat{H}(\mathbf{k})$ is the Hamiltonian at the wave number $\mathbf{k} = (k_x, k_y)$, and $E_{n,\mathbf{k}}$ is the eigenvalue with the band index n (= 1, 2, ..., 6). The eigenvector $|u_{n,\mathbf{k}}\rangle$ is written by

$$|u_{n,\mathbf{k}}\rangle = [c_{n,A}(\mathbf{k}), c_{n,B}(\mathbf{k}), c_{n,C}(\mathbf{k}), c_{n,D}(\mathbf{k}), c_{n,E}(\mathbf{k}), c_{n,F}(\mathbf{k})]^T,$$

where $[\cdots]^T$ means the transpose of vector. $c_{n,\alpha}(\mathbf{k})$ is the amplitude of the wave function at the site α for the *n*-th band. The tight-binding Hamiltonian up to the nearest-neighbor hopping

is

$$\hat{H}(\boldsymbol{k}) = -\gamma \begin{pmatrix} 0 & 1 & 0 & \rho_y & 0 & 1 \\ 1 & 0 & 1 & 0 & 0 & \rho_x^* \\ 0 & 1 & 0 & 1 & \rho_x^* & 0 \\ \rho_y^* & 0 & 1 & 0 & 1 & 0 \\ 0 & 0 & \rho_x & 1 & 0 & 1 \\ 1 & \rho_x & 0 & 0 & 1 & 0 \end{pmatrix},$$
(2)

with

$$\rho_x = \frac{\gamma}{\gamma} e^{i \boldsymbol{k} \cdot \boldsymbol{a}_1}, \, \rho_y = \frac{\gamma}{\gamma} e^{i \boldsymbol{k} \cdot \boldsymbol{a}_2}. \tag{3}$$

Figure 2 (a) shows the energy band structure along the path connecting high-symmetric points of the 1st BZ, and the density of states (DOS) for $\gamma'/\gamma = 1$. Since BPN has a π -electron per atomic site in average, the Fermi energy is E = 0. There are six energy bands, and from the bottom to the top, and the corresponding band index is 1 to 6. BPN is metallic with flat bands at E = 0. Also, owing to the crystal symmetry of BPN, the energy dispersion has the following relation,

$$E_n(k_x, k_y) = -E_{6-(n-1)}\left(k_x \pm \frac{\pi}{a}, k_y\right).$$
 (4)

Figure 2 (b) is the 3D plot of the energy band structure in the 1st BZ. It should be noted that the band touchings occur only on the the line of Γ -X. Figures 2 (c) and (d) show the energy band structure on Γ -X and Γ -Y lines, respectively. The 2nd and the 3rd subbands linearly cross at a point on Γ – X line, i.e., tilted Dirac cone. Similarly, the tilted Dirac cones also emerge between the 4th and the 5th subbands. However, the 3rd and the 4th subbands touch differently at E = 0, i.e., isotropic energy dispersion. At Γ point, these bands linearly touch along the k_x direction, whereas the 3rd subband becomes flat, and the 4th subband has a parabolic dispersion in k_y direction. Additionally, at X point, the 3rd subband is parabolic along X-S line, while the 4th subband is almost flat along X-S line.

B. Effect of variable hopping energy

Figures 3 (a)-(d) show the energy band structures of 2D BPN with several different ratios of hopping energy γ'/γ . It can be seen that the topology of the energy band structure crucially depends on the ratio of these two hopping parameters. In BPN, the topological phase transition occurs at $\gamma'/\gamma = 1/2$, 1, and 1.5, where the band gap closes and reopens. The closing and reopening of the energy band gap cause a band inversion, resulting in a topological phase transition, i.e., a change in the value of the Zak phase.

In the range of $1/2 \le \gamma'/\gamma \le 1$, the 1st subband touches the 2nd subband, similarly, the 5th subband touches the 6th subband. However, these band touchings are lifted for the other range and become isolated.

Furthermore, the 3rd and the 4th subbands touch at the Fermi energy in the range of $1 \le \gamma'/\gamma \le 1.5$. Therefore, a complete band gap opens when $\gamma'/\gamma < 1$ and $\gamma'/\gamma > 1.5$.



FIG. 2. (a) The energy band structure and the corresponding DOS for $\gamma'/\gamma = 1$. There are six subbands. (b) 3D plot of the energy band structure for the band-2, the band-3, and the band-4. (c) The energy band structure along k_x direction. Tilted Dirac dispersions can be seen on Γ -X line between the band-2 and the band-3. (d) The energy band structure along k_y direction. The band-3 is flat along the Γ -Y line, and the band-4 has a parabolic dispersion at Γ point.

There are four tilted Dirac cones on the Γ -X line; one is between the 2nd and the 3rd subbands, and another one is between the 4th and the 5 subbands. These crossing points are marked by green circles in Fig. 3. These four points are maintained in all cases.

III. TOPOLOGICAL PROPERTIES

A. Zak Phase and Topological Edge States

We numerically calculate Zak phase [26–31, 36] which is given as the line integral of Berry connection;

$$A_n(k_{\parallel},k_{\perp}) = i \langle u_{n,k} | \partial_{k_{\perp}} | u_{n,k} \rangle.$$
⁽⁵⁾

The Berry connection physically means the vector potential in the reciprocal space. In order to discuss the charge polarization based on the Zak phase, we have introduced two specific one-dimensional (1D) wave numbers, i.e., k_{\parallel} and k_{\perp} . Here, k_{\parallel} represents the 1D wave number parallel to the translational direction of the considered edge or ribbons. k_{\perp} is a crystal momentum perpendicular to k_{\parallel} .

Zak phase of the *n*-th subband is defined as

$$Z_n(k_{\parallel}) = \int_C dk_{\perp} A_n(k_{\parallel}, k_{\perp}), \qquad (6)$$

where *C* is a straight path along k_{\perp} connecting two equivalent points of *k* in the 2D BZ. For an inversion symmetric system, the Zak phase is quantized by 0 or π . Charge polarization for *n*-subband, P_n , is related with the Zak phase as

$$P_n = \frac{1}{2\pi} Z_n. \tag{7}$$

Thus, if the nontrivial Zak phase of π appears, we obtain the finite charge polarization at the surface or edge, which is nothing more than the edge states. Since the bulk topological properties are related to the charge polarization at edges, this is referred to as bulk-edge correspondence. The Zak phase approach successfully predicts the topological edge states (TES) for graphene, A3B nanosheet, 2D SSH model, and so on [31, 35, 36, 51].

Now, let us consider the 1D Biphenylene ribbons (BPRs). Figure 4 summarizes the lattice structure, electronic band structure and Zak phase for BPRs. To discuss the electronic properties of BPR, we shall define the translationl vector of BPR as $T = ma_1 + na_2 = T(m,n)$, and the corresponding reciprocal vector as $\Gamma_{\parallel} = 2\pi \frac{T}{|T|^2}$. Figure 4 (a) displays the schematic of BPR with zigzag edges (zigzag-BPR), where *N* is the width of ribbons. Since the translational vector of zigzag-BPR is given as T = T(1,0), the 1st BZ of zigzag-BPR is given as $|k_x| \le \pi/a$, which are marked as thick magenta lines in Fig. 4 (b). The integration path *C* for the calculation of the Zak phase is given in cyan arrow in Fig. 4 (b). The energy band structure for zigzag-BPR with N = 50 is shown in Fig. 4 (c), where black lines indicate the modes of bulk states, and cyan lines indicate the modes of topological edge states, respectively.

For a numerical calculation, we rewrite Eq. (6) as a discrete form using Taylor expansion up to the first order, i.e.,

$$Z_n(k_{\parallel}) = -\mathrm{Im}\left[ln\left(\prod_{j=l}^{N_0} \langle u_{n,k_{\perp j}} | u_{n,k_{\perp j+l}} \rangle\right)\right],\tag{8}$$

where k_{\parallel} is a 1D momentum space parallel to T. The integral path is divided into N_0 segments along k_{\perp} . Here, we impose for the wave function a gauge-fixing condition $|\langle \phi_g | u_{n,k_j} \rangle| \neq 0$ in all k_j point on the path with a global gauge ϕ_g , which is well-defined in the whole BZ [52].

The emergence of TES in zigzag-BPR can be associated with the nontrivial Zak phase of π . Figure 4 (d) shows the *k*-dependent Zak phase of zigzag-BPR for the lowest three bands. The Zak phase of the 1st subband is always 0 for any *k*, i.e., topological trivial. However, in the 2nd and the 3rd subbands, there are *k*-regions ($|k| > k_c$) with finite Zak phase of π , i.e., topologically nontrivial. Here, $\pm k_c$ is the position



FIG. 3. Energy band structure of 2D BPN for (a) $\gamma'/\gamma = 1/3$, (b) $\gamma'/\gamma = 1/2$, (c) $\gamma'/\gamma = 1.5$, and (d) $\gamma'/\gamma = 2$. The band degenerating points are marked with green circles.



FIG. 4. (a) Schematic lattice structure of BPN ribbon (BPR) with zigzag edges. *N* is the width of the ribbon. The translational vector T for zigzag BPR is defined as T = T(1,0). Here, $T = ma_1 + na_2 = T(m,n)$. (b) The 1st BZ of zigzag BPR (thick magenta line). The shaded yellow area is the 1st BZ of 2D BPN. In zigzag BPR, its 1st BZ is projected onto k_x -axis and given as $-\pi/a \le k_x \le \pi/a$. The integration path *C* for the calculation of the Zak phase is taken along k_y . (c) Energy band structure for zigzag BPR for N = 50. Cyan lines indicate the modes of TES that emerge in the energy gaps where the total Zak phase is π . (d) The corresponding Zak phase of zigzag BPR for the lowest three subbands, where Zak phase is finite in the 2nd and the 3rd subbands. (e) Schematic lattice structure of BPR with armchair edges. *N* is the width of the ribbon. The translational vector T for armchair BPR is defined as T = T(0, 1). (f) The 1st BZ of zigzag BPR (thick magenta line). The shaded yellow area is the 1st BZ of 2D BPN. In armchair BPR, its 1st BZ is projected onto k_y -axis and given as $-\pi/a_T \le k_y \le \pi/a_T$. The integration path *C* for the calculation of the Zak phase is taken along k_x . (g) Energy band structure for armchair BPR for N = 50. Cyan lines indicate the modes of TES that emerge in the energy gaps where the total Zak phase is π . (h) The corresponding Zak phase for armchair BPR for the lowest three subbands, where Zak phase is finite in the 2nd and the 3rd subbands.

of Dirac point between 2nd and 3rd subbands. Thus, the TES emerge in the energy gap between the 2nd and the 3rd subbands in the region of $|k| > k_c$, because $\sum_{n=1}^2 Z_n(k) = \pi$ for $|k| < k_c$. However, since $\sum_{n=1}^3 Z_n(k) = 0$ for any k, there is no TES in the energy gap between the 3rd and the 4th subbands. Other TES above E > 0 are also explained in a similar manner.

Next, we shall analyze the electronic and topological properties of BPR with armchair edges (armchair-BPR). Figure 4 (e) displays the schematic of armchair-BPR, where N is the width of the ribbon. The translational vector of armchair-BPR is given as T = (0, 1). Thus, the 1st BZ of armchair-BPR is given as $|k_y| \le \pi/a_T$, which are marked as thick cyan line in Fig. 4 (f). The energy band structure of armchair-BPR with N = 50 is shown in Fig. 4 (g), where the cyan lines in the energy gaps indicate TES modes.

The emergence of TES modes in armchair-BPR is also clearly explained by the analysis of the Zak phase. Figure 4 (h) displays the *k*-dependent Zak phase for the lowest three subbands of armchair-BPR, which gives π , 0, π from the lowest subband. Thus, the energy band gaps between the 1st and the 2nd subbands becomes topologically nontrivial, because $Z_1(k) = \pi$. Similarly, the energy band gaps between the 2nd and the 3rd subbands becomes topologically nontrivial, because $\sum_{n=1}^{2} Z_n(k) = \pi$. These results are consistent with the emergence of TES shown in Figure 4 (g). Other TES above E > 0 are also explained similarly.

Similarly, from the viewpoint of Zak phase, it is illustrated that the existence of TES, even if we tune the ratio of hopping energy, i.e., γ'/γ . Figures 5 (a) and (b) display the energy band structures (upper) and the corresponding Zak phase (lower panel) for zigzag- and armchair-BPR, respectively, with the ratio of hopping parameters tuned to $\gamma'/\gamma = 1/2$ and 2. For all cases of zigzag-BPR shown in Fig. 5 (a), the emergence of TES is consistent with the finite Zak phase of π . For armchair-BPR shown in Fig. 5 (b), the emergence of TES for $\gamma'/\gamma = 1/2$



FIG. 5. Energy band structure of BPR and the corresponding Zak phase. (a) Zigzag-BPR with $\gamma'/\gamma = 1/2$ (left) and $\gamma'/\gamma = 2$ (right). In these case, TES (cyan lines) emerge in the energy gap where Zak phase has π . (b) Armchair-BPR with $\gamma'/\gamma = 1/2$ (left) and $\gamma'/\gamma = 2$ (right). TES with cyan lines appear in the energy gap that Zak phase has π . However, TES with magenta lines emerge in the energy band gap that Zak phase has 2π . The puzzle will be resolved by considering Wannier centers (see main text).

(left panel) is consistent with the presence of nontrivial Zak phase of π . For $\gamma'/\gamma = 2$ (right panel), the emergence of two TES modes with magenta lines in the gap between the 3rd and the 4th bands can not be illustrated solely by Zak phase, because $\sum_{n=1}^{3} = 2\pi$. Since the Zak phase of 2π is identical to the Zak phase of 0, TES should not appear. For armchair-BPR, in general, two TES modes appear in the band gap between the 3rd and the 4th bands for $\gamma'/\gamma > 1$, in spite of that Zak phase is 2π . This puzzle can be explained by counting the Wannier centers using elementary band representation in the following section.

B. Elementary band representation

In the previous section, we showed that the Zak phase determines the existence of the edge states by numerical calculation. However, the ambiguity for the number of edge states has remained, because the Zak phase only gives the parities of \mathbb{Z}_2 value, e.g., the summation of the Zak phase of the occupied bands becomes 0 even if there are two edge states in the gap. In order to obtain the accurate number of edge states, we introduce the symmetry analysis using the irreducible representation (irrep) at high-symmetric points of the 1st BZ [53– 58].

The number of edge states is deeply involved with the central position of Wannier states (Wannier center) [29, 53, 59, 60]. The edge terminated line crosses Wannier orbital *n* times in a period of the unit cell, *n* edge states exist in the gap. The Wannier center is located at the midpoint of the bond with the stronger hopping energy. As discussed before, we considered two types of hopping energies between two atomic sites, i.e., γ and γ' . Here, we identify the position of the Wannier center in terms of the ratio γ'/γ .

To show the relationship between the position of the Wannier center and the stronger hopping bond, we classify the energy bands of BPN by the irreps of high-symmetric points in the 1st BZ. The space group of BPN is *Pmmm* which belongs to point group D_{2h} , and there are eight irreps as shown in Table I. Here, C_{2j} (j = x, y, z) is the 2-fold rotation around *j*-axis, *I* is the inversion, σ_j is the mirror reflection with respect to *kl*plane (j, k, l = x, y, z).

TABLE I. The character table of point group D_{2h} . The four high-symmetric points in the 1st BZ belong to the pont goup D_{2h} .

D_{2h}	Ε	C_{2z}	C_{2y}	C_{2x}	Ι	σ_z	σ_y	σ_x
Γ_1^+	1	1	1	1	1	1	1	1
Γ_2^+	1	1	-1	-1	1	1	-1	-1
Γ_3^{\mp}	1	-1	1	-1	1	-1	1	-1
Γ_4^+	1	-1	-1	1	1	-1	-1	1
Γ_1^{\perp}	1	1	1	1	-1	-1	-1	-1
Γ_2^{\perp}	1	1	-1	-1	-1	-1	1	1
$\Gamma_3^{\tilde{-}}$	1	-1	1	-1	-1	1	-1	1
Γ_4^{-}	1	-1	-1	1	-1	1	1	-1



FIG. 6. The irreps of the occupied energy bands for $\gamma' > \gamma$. Note that only the lowest three energy bands of 2D BPN are displayed.

Each of the six bands in BPN is classified by the irreps at high-symmetric points of the 1st BZ. Since four highsymmetric points in the 1st BZ have the same symmetry as BPN lattice, the irreps at Γ , X, Y, and S points are identical to



FIG. 7. (a) Wyckoff positions (WPs) on *xy*-plane for the space group *Pmmm*. WPs 2*i*, 2*k*, 2*m*, 2*o* are two positions on the green lines. In the case of γ' (gray line) > γ (red line), the occupied three bands of BPN consist of two elementary bands b_{17} (WP 1*e*) and b_{45} (WP 2*o*) in Table II. (b) (top) Since the edge terminated line of zigzag-BPR crosses Wannier orbital (indicated by the blue ellipse) once, one edge state appear. On the other hand, (bottom) the edge terminated line of armchair-BPR crosses Wannier orbitals (the red ellipse) twice, that result in two edge states.

the point group D_{2h} . In Fig. 6, we show the correspondence between the occupied bands of BPN and the irreps characterized by the symmetry of the wave function. From Fig. 6, we can define the character of the occupied bands by a single vector

$$\boldsymbol{b} = (\gamma_1^+, \gamma_2^+, \gamma_3^-, \gamma_4^-; x_1^+, x_2^+, x_3^-, x_4^-; \\ y_1^+, y_2^+, y_3^-, y_4^-; s_1^+, s_2^+, s_3^-, s_4^-),$$
(9)

where γ_n^{\pm} , x_n^{\pm} , y_n^{\pm} , and s_n^{\pm} with n = 1, 2, ...4 is the number of the bands whose wave function at Γ , X, Y, and S points have an irrep Γ_n^{\pm} . Here, we omitted the irreps Γ_3^+ , Γ_4^+ , Γ_1^- , and $\Gamma_2^$ which are related to the parity with respect to the *xy*-plane, i.e., the symmetry operation of σ_z , because our tight-binding model is essentially assuming the *s*-orbital as atomic orbitals which give always positive parity with respect to the operation of σ_z and become irrelevant. If we replace the atomic orbital on each site from *s*-orbital to p_z -orbital, we need to take into account irreps Γ_3^+ , Γ_4^+ , Γ_1^- , and Γ_2^- , but the discussion and the result will not be essentially changed. Thus, the vector of the occupied π -bands of BPN is described as

$$\boldsymbol{b}_{p_z} = (2,0,1,0;1,1,0,1;1,0,2,0;0,1,1,1).$$
(10)

Here, we list all elementary bands allowed in the space group *Pmmm* in Table II. An elementary band is a set of atomic orbitals situated at the symmetry protected position, which is called a Wyckoff position (WP). The WP is classified by the site symmetry group (SSG), which guarantees that the WP is invariant in the unit cell. In Fig. 7 (a), we show WPs in the unit cell. For instance, there are eight WPs which have the highest symmetry with the coordinates 1a: (0,0,0), $1b: (a,0,0), 1c: (0,0,z), \ldots, 1h = (a,a_T,z)$, and their SSG is identical to the point group of the lattice, and has eight irreps. The WPs (and their coordinates) and the corresponding SSG are shown in the first and the second column of Table II.

Atomic orbitals located at WPs have irreps characterized by SSGs, which are the subgroups of the space group of the crystal. Each arrangement of the atomic orbitals is called the elementary band, and the irreps of the elementary band are elementary band representations (EBRs). In Table II, we show all possible EBRs of WP on *xy*-plane. There are fifty different elementary bands with a serial number η (= 1, 2, ..., 50).

In the same manner as Eq. (9), we shall describe the elementary bands labeled by η as

$$\boldsymbol{b}_{\eta} = (\gamma_{1}^{+(\eta)}, \gamma_{2}^{+(\eta)}, \gamma_{3}^{-(\eta)}, \gamma_{4}^{-(\eta)}; x_{1}^{+(\eta)}, x_{2}^{+(\eta)}, x_{3}^{-(\eta)}, x_{4}^{-(\eta)}; y_{1}^{+(\eta)}, y_{2}^{+(\eta)}, y_{3}^{-(\eta)}, y_{4}^{-(\eta)}; s_{1}^{+(\eta)}, s_{2}^{+(\eta)}, s_{3}^{-(\eta)}, s_{4}^{-(\eta)}).$$
(11)

Actual elements of b_{η} are listed from the 4th to the 19th column in Table II, where that Bloch function $e^{i\mathbf{k}\cdot\mathbf{R}}$ is taken into account in each character. For example, the EBR of WP 1*a* with $\mathbf{R} = (0,0)$ gives identical irreps among Γ , X, Y, S points. In contrast, the EBR of WP 1b with $\mathbf{R} = (a,0)$ changes the sequence of the irreducible representations at the X and S points depending on the Bloch phase. The Wannier orbitals are the combination of the elementary bands, and their central positions are the corresponding WPs in the unit cell. As shown in the bottom row of Table II, the Wannier orbitals of occupied three bands of BPN can be described as

$$\boldsymbol{b}_{p_z} = \sum_{\eta} n_{\eta} \boldsymbol{b}_{\eta}, \qquad (12)$$

where n_{η} is zero or positive number. From Table II, n_{η} is zero except for two EBRs; $\eta = 17$ and $\eta = 45$ whose WPs are 1eand 20, and correspond to SSGs mmm and m2m respectively. Therefore, the occupied bands of BPN are the linear combination of the two elementary bands b_{17} and b_{45} which are both s-like orbitals situated at WPs 1e and 2o. Hence, the Wannier orbitals are situated at the stronger hopping bonds, and the exact number of the edge states can be determined. Figure 7 (b) illustrates the broken Wannier orbitals at the zigzag and armchair edge boundaries for $\gamma' > \gamma$. If the strength of the hopping energy is opposite ($\gamma' < \gamma$), Wannier orbitals should be situated at the 6-membered rings (indicated by the red line), not the edge boundaries. Recalling that 2π Zak phase leads to either zero ($\gamma' < \gamma$) or two ($\gamma' > \gamma$) edge states in Sec. III A, it can be understood that the number of broken Wannier orbitals at the edge boundary consistent with the number of edge states.

C. Topological Corner States

In this section, we consider BPN nanoflake to investigate the conditions for the appearance of topological corner states as "edge-of-edge" states [61–65]. In a similar manner to that

WP	SSG	irrens	v^+	v^+	ν	v ⁻	r^+	r^+	<i>r</i> ⁻	r^{-}	v ⁺	v ⁺	v ⁻	v ⁻	e+	e+	e	e	n
	550	Γ^+	$\frac{r_1}{1}$	<u>12</u>	13	14	1 1	¹	¹ 3	¹ 4	y ₁ 1	$\frac{y_1}{0}$	y ₃	y ₄	<u>31</u> 1	<u>31</u>	<u>33</u>	<u>34</u>	1
$1a \\ (0,0)$		Γ^+	0	1	0	0	0	1	0	0	0	1	0	0	0	1	0	0	2
		Γ^+	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	2
		Γ^+	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	1
	ттт	Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	5
		Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	6
		Γ^{-}	0	0	1	0	0	0	1	0	0	0	1	0	0	0	1	0	7
		Γ^{-}	0	0	0	1	0	0	0	1	0	0	0	1	0	0	0	1	8
		$\frac{\Gamma_4}{\Gamma^+}$	1	0	0	0	0	0	0	1	1	0	0	0	0	0	0	1	0
		Γ^+	0	1	0	0	0	0	1	0	0	1	0	0	0	0	1	0	10
		Γ^{+}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	11
1b		Γ^+	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	12
(a, 0)	mmm	Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	12
()-)		Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	14
		Γ^{1}_{2}	0	0	1	0	0	1	0	0	0	0	1	0	0	1	0	0	14
		Γ^{-}	0	0	1	1	1	0	0	0	0	0	1	1	1	1	0	0	15
		$\frac{\Gamma_4}{\Gamma^+}$	1	0	0	1	1	0	0	0	0	0	1	1	1	0	1	0	10
		Γ^+	1	1	0	0	1	1	0	0	0	0	1	1	0	0	1	1	17
		Γ^+	0	0	0	0	0	0	0	0	0	0	0	1	0	0	0	1	10
1e		Γ^+	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	20
$(0,a_T)$	mmm	Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	20
(0,01)		Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	21
		Γ^{1}_{2}	0	0	1	0	0	0	1	0	1	0	0	0	1	0	0	0	22
		Γ^{-}	0	0	1	1	0	0	1	1	1	1	0	0	1	1	0	0	23
		Γ^+	1	0	0	1	0	0	0	1	0	1	1	0	1	1	0	0	24
		Γ^+	1	1	0	0	0	0	1	1	0	0	1	1	1	1	0	0	25
		Γ^{+}	0	1	0	0	0	0	1	0	0	0	0	1	0	1	0	0	20
1f		Γ^+	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	27
$(a a_T)$	mmm	Γ^{-}_{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	20
(u,u)		Γ^{-}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	29 30
		Γ^{-}	0	0	1	0	0	1	0	0	1	0	0	0	0	0	1	0	31
		Γ_3	0	0	1	1	1	0	0	0	1	1	0	0	0	0	1	1	31
		<u>г</u> 4	1	0	0	1	1	0	0	1	1	1	0	1	1	0	0	1	32
2:			1	0	0	1	0	0	0	1	1	0	0	1	1	0	0	1	33
$(+x \ 0)$	2mm	Г <u>2</u> Га	0	1	1	0	0	1	1	0	0	1	1	0	0	1	1	0	35
(±1,0)		Γ_{4}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	36
			1	0	0	1	1	0	0	1	0	1	1	0	0	1	1	0	37
2k		Γ_2	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	38
$(\pm x, a_T)$	2mm	Γ_2	0	1	1	0	0	1	1	0	1	0	0	1	1	0	0	1	39
()		Γ_{4}	0	0	0	0	0	0	0	Ő	0	0	0	0	0	0	0	0	40
$2m \\ (0,\pm y)$		<u>-</u> 4 Γ1	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	41
	_	Γ_2	0	0	0	0	0	0	0	Ő	0	0	0	Ő	0	0	0	0	42
	m2m	Γ_3	0	1	0	1	0	1	0	1	0	1	0	1	0	1	0	1	43
		Γ_4^{j}	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	44
		Γ_1	1	0	1	0	0	1	0	1	1	0	1	0	0	1	0	1	45
2o $(a,\pm y)$	~	Γ_2	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	46
	m2m	Γ_3	0	1	0	1	1	0	1	0	0	1	0	1	1	0	1	0	47
/		Γ_4	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	48
4y		Γ_1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	1	49
$(\pm x, \pm y)$	<i>m</i>	Γ_2	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	50
b_{p_z} (occu	pied p_z	bands)	2	0	1	0	1	1	0	1	1	0	2	0	0	1	1	1	17 + 45

TABLE II. Elementary band representations (EBRs) of the space group Pmmm.

shown in the previous section, we assume a geometry in which the Wannier orbitals are isolated at the boundary of the system. Figure 8 illustrates the structure of the BPN nanoflake formed as a combination of diagonally cut lines. The rhombus shaded by yellow is a unit, which is periodic in the m and *n* directions. Here, the red lines indicate the hopping of γ and the other black lines indicate the hopping γ' . For $\gamma' > \gamma$, edge states exist in the energy gap, where the Wannier orbitals are located on the bonds indicated by the red ellipses as shown in the zoom of Figure 8. Furthermore, if the basis of atomic sites



FIG. 8. The structure of the BPN nanoflake for $\gamma' > \gamma$. The red ellipses indicate the Wannier orbitals. Deleting the atom basis indicated black dots at the four corners, there are $(m \times n \times 12 - 6)$ atom sites. Wannier orbitals are cut by the corner geometries resulting in uncoupled Wannier orbitals at the corner sites.

marked by the black circles at the four corners is removed, the Wannier orbitals are broken at the corner sites, i.e., the emergence of corner states.

Figure 9 (a) shows the energy spectrum of the nanoflake, and the right figure is a zoomed-in view near zero energy. Since the system includes 1194 atoms in the case of (m, n) =(10, 10), the site index has that same number. For $\gamma' > \gamma$, it has an energy gap near zero energy, and six isolated energy levels are found within the gap. Figure 9 (b) is the wave function of the six states within the gap near zero energy. We plot the amplitude of the wave function as the radius of the circles. We can see the exponentially localized states at the corners of the nanoflake. Two states with E = 0 are localized in the left and right corners, while the other four states are localized in the lower and upper corners. This can be understood from the position of the Wannier orbitals. The Wannier orbitals cut by the corner geometry are present: one at the left and right corners and two at the upper and lower corners, resulting in a corresponding number of corner states. Therefore, we can see that these corner states are due to the uncoupled Wannier orbitals at the corners of the system. In addition, changing the values of *m* and *n* does not affect the appearance of corner states.

IV. CONCLUSION

In this paper, we have studied the electronic and topological properties of BPN. We have demonstrated that BPN exhibits flat bands and tilted Dirac cones, and these tilted cones persist even when the strength of electron hoppings is modified. By varying the ratio of hopping energies, specifically the ratio between intra-cellular hopping γ and inter-cellular hopping γ' , we can open an energy band gap, leading to a topological phase transition. The emergence of edge states is guaranteed by a nonzero Zak phase, and the number of edge states aligns with the number of Wannier orbitals at the edge boundary. Using the same principle, we have illustrated the existence of corner states in systems where uncoupled Wannier orbitals are located at the corners. The present theoretical approach is applicable to the design of new materials that share the same structure as BPNs. Although it is very hard to tune the electron hopping energies in actual BPN materials, we can design the system having the topological properties of BPN based on photonic crystals. The extension to the photonic crystals will be discussed elsewhere.

ACKNOWLEDGMENTS

The authors are grateful to M. Hitomi for helpful discussions. This work was supported by JSPS KAKENHI (Nos. 22H05473, JP21H01019, JP18H01154) and JST CREST (No. JPMJCR19T1).

Appendix A: tight-binding parameters of 2D BPN

In this section, we present the parameter set for the tightbinding model to describe π -electronic states of 2D BPN. We have implemented the first-principles calculations to obtain the energy band structure for 2D BPN based on the density functional theory (DFT). To this end, we have used the QunatumEspresso package [66, 67] by employing the PBE variant of the GGA method [68]. A relaxation of the structure was achieved by considering a magnitude of the forces on each atom that is less than 13.6×10^{-4} eV/Å. A $12 \times 14 \times 1$ Monkhorst–Pack mesh [69] is used to sample the 1st BZ for structural relaxation. Figure 10(a) shows the obtained π electronic energy band structures of 2D BPN (dashed line).

In further, we have extracted the tight-binding parameters for π -electrons of 2D BPN using the Wannier90 package [70]. The parameter set reproduces quite well the energy band structure obtained by DFT as shown in Fig. 10 (a), where the solid lines are the tight-binding calculation obtained by Wannier90.

Figures 10 (b) and (c) are schematic for the positions of the hopping integrals for tight-binding model, where the nearest neighbor (n.n.) hoppings are shown in Fig 10(b). Similarly, the 2nd and the 3rd n.n. hoppings are shown in Fig 10(c). The obtained electron hopping parameters are listed in Table III. Figure 10(d) shows the energy band structure of π -electrons for 2D BPN. The dashed lines indicate the band structure, which only includes n.n. hoppings. However, the solid lines indicate the energy band structure, which includes up to 3rd n.n. hoppings. The inclusion up to 3rd n.n. hoppings sufficiently well reproduce the energy band structure obtained by DFT. Especially, 3rd n.n. hoppings are necessary to reproduce the band crossing between 3rd and 4th subbands on the Y- Γ line, the band gap opening at X and the slight tilt of the flat band on X-S line.



FIG. 9. (a) The energy spectrum of the BPN nanoflake. (b) The amplitude of the wave function of the six energy levels in the gap. Two states are localized at the left and right corner, and the other four states are localized at the upper and lower corner.



FIG. 10. (a) Energy band structure obtained by DFT (dashed line) and Wannier90 (solid line). In Wanner90 calculation, only p_z orbitals of carbon atoms are taken into account for the projection. (b) Schematic of BPN lattice structure with the definition of nearest neighbor (n.n.) hoppings for the tight-binding model of 2D BPN. Yellow shaded rectangle is unit cell. γ_0 is intra-cellular n.n. hoppings for the bond of B-C and E-F. γ_0 is intra-cellular n.n. hoppings for the bond of A-B, C-D, D-E and F-A. γ'_x and γ'_y are the inter-cellular hoppings for x- and y-directions, respectively. (c) The definition of 2nd n.n. and 3rd n.n. electron hoppings. Magenta thick dashed lines indicate the 2nd n.n. hoppings. τ_0 is intra-cellular hoppings for the bond of A-E, A-C. τ'_y is inter-cellular hoppings for the bond of A-B, A-F. Cyan dot lines indicate the 3rd n.n. hoppings. ζ_0 is intra-cellular hoppings for the bond of A-D. ζ_1 is intra-cellular hoppings for the bond of B-C and E-II. (d) Energy band structure of effective tight-binding model considering up to the n.n. hopping (dashed line) and the 3rd n.n. hopping (solid line). Inclusion up to 3rd n.n. hoppings sufficiently well reproduces the energy band structures obtained by DFT shown in (a).

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TABLE III. Tight-binding parameters for 2D BPN. The values are derived from the Wannier90 calculation. The set of these parameters well reproduces the energy band structures of π -electrons for 2D BPN as shown in Fig. 10 (d). The list of the hopping integrals. V_{α} (V_{β}) is the on-site potential energy on A, D (B, C, E, F) sites, respectively. The definition electron hoppings on the lattice of 2D BPN are shown in Figs. 10 (b) and (c).

pote	ntial		n.			2nd n.n.		3rd n.n.			
V_{α}	V_{β}	Yo	γ_1	γ'_x	γ'_{y}	$ au_0$	$ au_x'$	$ au_{y}'$	ζ0	ζ1	ζ'_{y}
-2.0742	-2.3647	-2.9603	-2.6910	-2.7479	-2.7962	0.2880	0.3969	0.2473	-0.2041	-0.2991	-0.1920

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